### ST 2SC1740

NPN Silicon Epitaxial Planar Transistor for switching and AF amplifier applications.

The transistor is subdivided into four groups Q, R, S and E. according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Collector 3. Base

TO-92 Plastic Package Weight approx. 0.19g

#### Absolute Maximum Ratings $(T_a = 25?)$

	Symbol	Value	Unit
Collector Base Voltage	V <sub>CBO</sub>	60	V
Collector Emitter Voltage	V <sub>CEO</sub>	50	V
Emitter Base Voltage	V <sub>EBO</sub>	5	V
Collector Current	I <sub>C</sub>	150	mA
Power Dissipation	P <sub>tot</sub>	300	mW
Junction Temperature	Tj	150	°C
Storage Temperature Range	Ts	-55 to +150	°С

### G S P FORM A IS AVAILABLE



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## Characteristics at T<sub>amb</sub>=25 °C

	Symbol	Min.	Тур.	Max.	Unit
DC Current Gain					
at $V_{CE}$ =6 $V$ , $I_{C}$ =1 $mA$	) h <sub>FE</sub>	120	-	270	-
F	R h <sub>FE</sub>	180	-	390	-
\$	h <sub>FE</sub>	270	-	560	-
E	h <sub>FE</sub>	390	-	820	-
Collector Base Breakdown Voltage					
at I <sub>C</sub> =50μA	$V_{(BR)CBO}$	60	-	-	V
Collector Emitter Breakdown Voltage					
at I <sub>C</sub> =1mA	$V_{(BR)CEO}$	50	-	-	V
Emitter Base Breakdown Voltage					
at I <sub>E</sub> =50μA	$V_{(BR)EBO}$	5	-	-	V
Collector Cutoff Current					
at V <sub>CB</sub> =60V	I <sub>CBO</sub>	-	-	0.1	μΑ
Emitter Cutoff Current					
at V <sub>EB</sub> =5V	I <sub>EBO</sub>	-	-	0.1	μΑ
Collector Saturation Voltage					
at I <sub>C</sub> =50mA, I <sub>B</sub> =5mA	$V_{CE(sat)}$	-	-	0.4	V
Gain Bandwidth Product					
at V <sub>CE</sub> =12V, I <sub>C</sub> =2mA	$f_{T}$	-	180	-	MHz
Output Capacitance					
at V <sub>CB</sub> =12V, f=1MHz	Сов	-	2	3.5	pF

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